TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

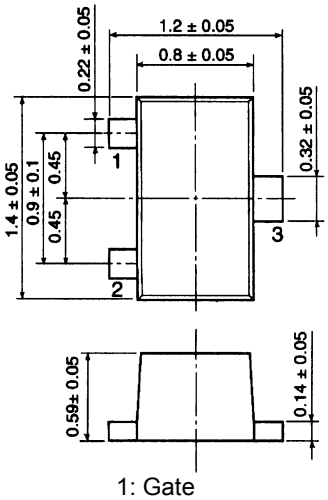
SSM3J16TE

High Speed Switching Applications

Analog Switch Applications

- Small package
- Low on-resistance : R_{on} = 8 Ω (max) (@V_{GS} = −4 V)
  : R_{on} = 12 Ω (max) (@V_{GS} = −2.5 V)
  : R_{on} = 45 Ω (max) (@V_{GS} = −1.5 V)

Unit: mm



1: Gate
2: Source
3: Drain

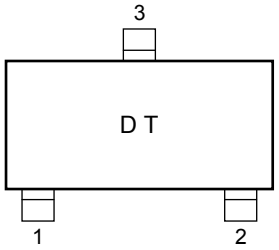
TESM	
JEDEC	—
JEITA	—
TOSHIBA	2-1B1B

Absolute Maximum Ratings (Ta = 25°C)

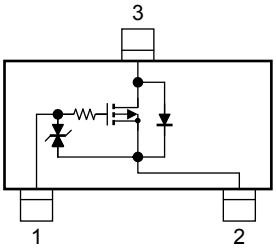
Characteristics		Symbol	Rating	Unit
Drain-Source voltage		V_{DS}	−20	V
Gate-Source voltage		V_{GSS}	±10	V
Drain current	DC	I_D	−100	mA
	Pulse	I_{DP}	−200	
Drain power dissipation (Ta = 25°C)		P_D	100	mW
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking



Equivalent Circuit (top view)



Handling Precaution

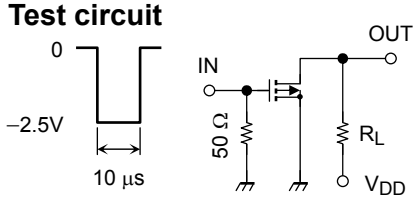
When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against static electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	MIN.	TYP.	MAX.	UNIT
Gate leakage current		I_{GSS}	V_{GS} = ±10 V, V_{DS} = 0	—	—	±1	μA
Drain-Source breakdown voltage		$V_{(BR)\ DSS}$	I_D = −0.1 mA, V_{GS} = 0	−20	—	—	V
Drain cut-off current		I_{DSS}	V_{DS} = −20 V, V_{GS} = 0	—	—	−1	μA
Gate threshold voltage		V_{th}	V_{DS} = −3 V, I_D = −0.1 mA	−0.6	—	−1.1	V
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = −3 V, I_D = −10 mA	25	—	—	mS
Drain-Source ON resistance		$R_{DS\ (ON)}$	I_D = −10 mA, V_{GS} = −4 V	—	6	8	Ω
			I_D = −10 mA, V_{GS} = −2.5 V	—	8	12	
			I_D = −1 mA, V_{GS} = −1.5 V	—	18	45	
Input capacitance		C_{iss}	V_{DS} = −3 V, V_{GS} = 0, f = 1 MHz	—	11	—	pF
Reverse transfer capacitance		C_{rss}		—	3.7	—	pF
Output capacitance		C_{oss}		—	10	—	pF
Switching time	Turn-on time	t_{on}	V_{DD} = −3 V, I_D = − 10 mA, V_{GS} = 0 ~ −2.5 V	—	130	—	ns
	Turn-off time	t_{off}		—	190	—	

Switching Time Test Circuit

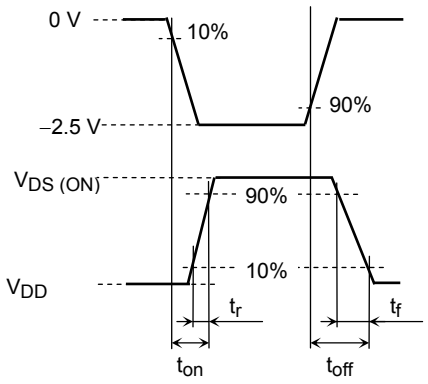
(a) Test circuit



V_{DD} = −3 V
Duty ≦ 1%
V_{IN}: t_r, t_f < 5 ns
(Z_{out} = 50 Ω)
Common Source
Ta = 25°C

(b) V_{IN}

(c) V_{OUT}

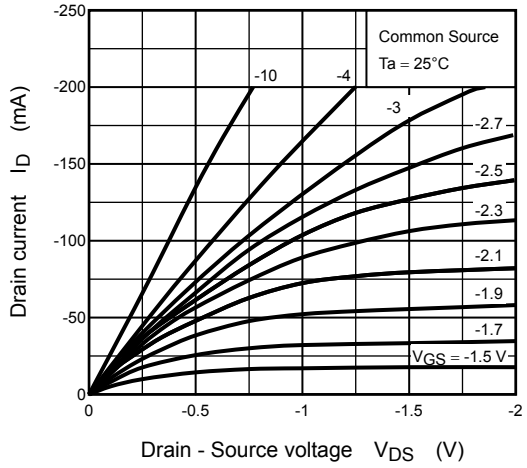


Precaution

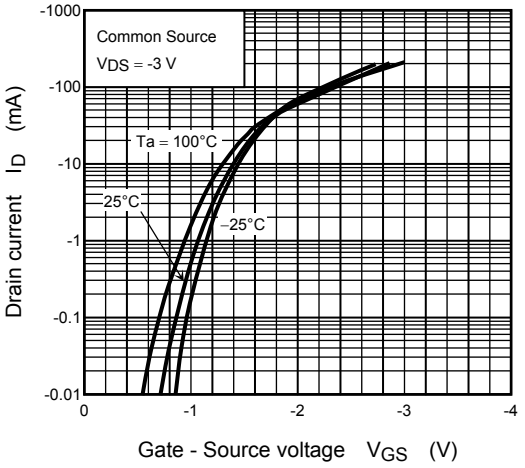
V_{th} can be expressed as the voltage between the gate and source when the low operating current value is I_D = 100 μA for this product. For normal switching operation, $V_{GS\ (on)}$ requires a higher voltage than V_{th} and $V_{GS\ (off)}$ requires a lower voltage than V_{th}. (The relationship can be established as follows: $V_{GS\ (off)} < V_{th} < V_{GS\ (on)}$.)

Be sure to take this into consideration when using the device.

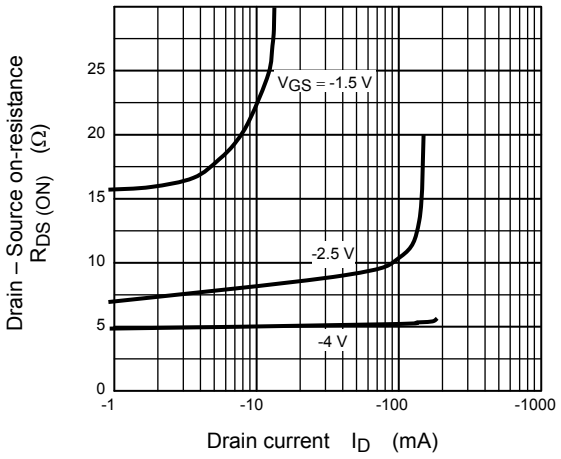
$I_D - V_{DS}$



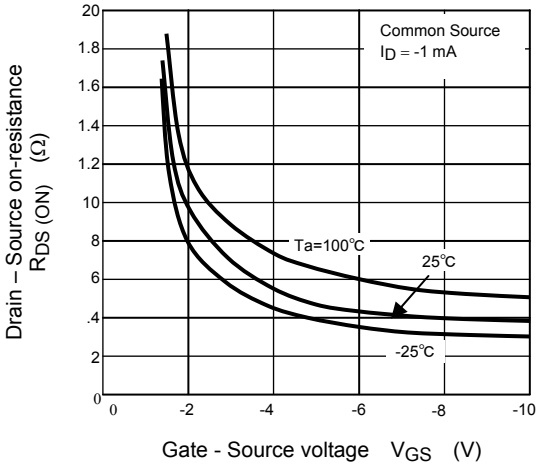
$I_D - V_{GS}$



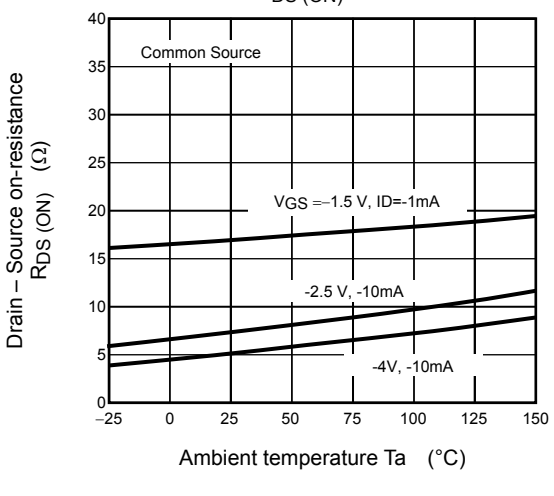
$R_{DS\ (ON)} - I_D$



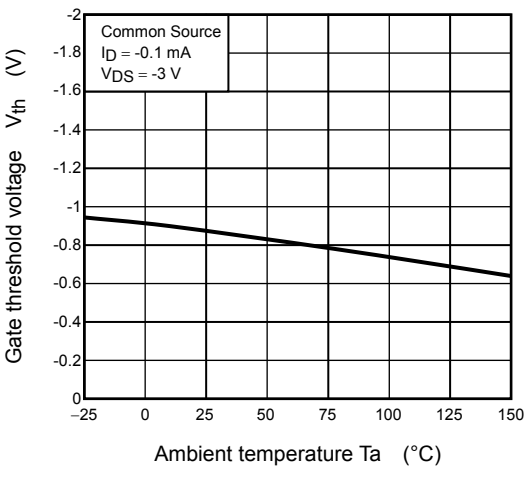
$R_{DS\ (ON)} - V_{GS}$



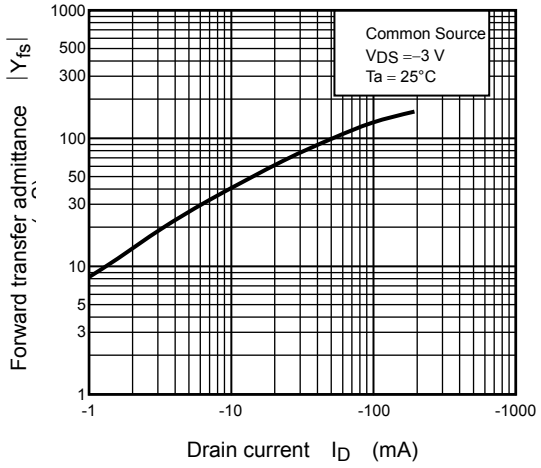
$R_{DS\ (ON)} - Ta$



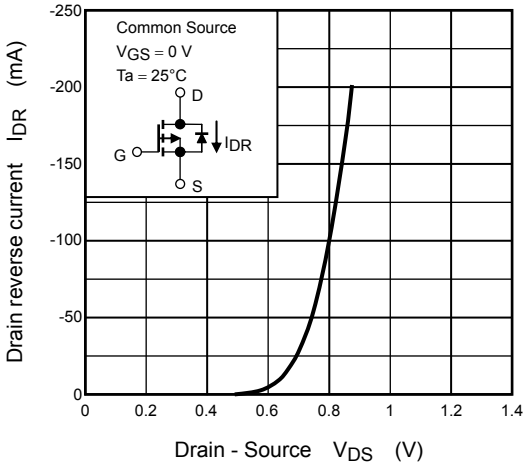
$V_{th} - Ta$



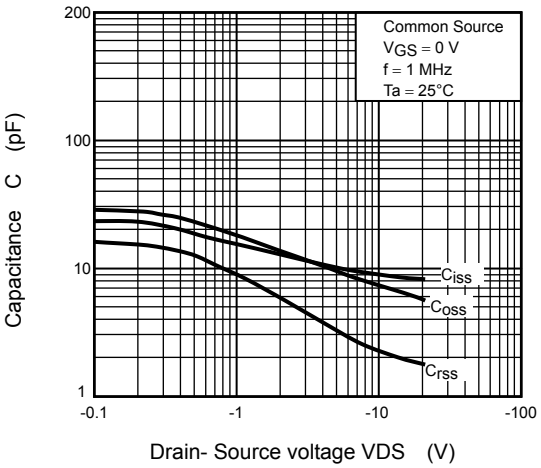
$|Y_{fs}| - I_D$



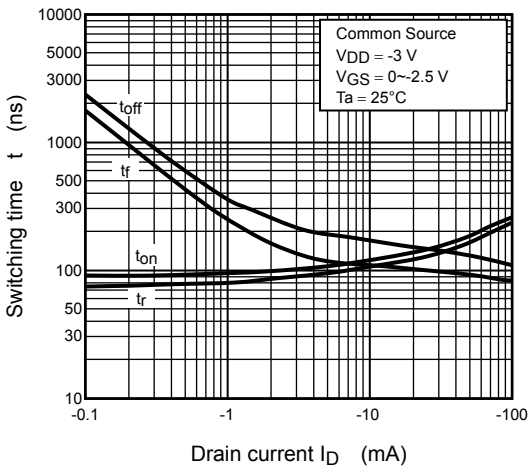
$I_{DR} - V_{DS}$



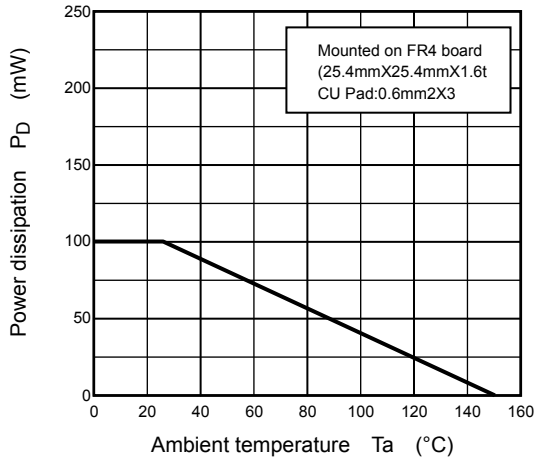
$c - V_{DS}$



$t - I_D$



$P_D - Ta$



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20070701-EN GENERAL

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